ERRATA

Equilibrium Shape of Si
[Phys. Rev. Lett. 70, 1643 (1993)]

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The Si step energy of 28 ± 10 meV/atom determined from the curvature of small voids near (100) should more properly be compared with half of the double \( A \)-type step energy (i.e., 0.5 \( \times \) 50 meV/atom) as opposed to the single \( B \)-type step energy (23 meV/atom) used in this paper. The authors would like to thank Dr. H. J. W. Zandvliet for pointing this out.


Singular Behavior of Shear Flow Far from Equilibrium

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The matrix \( \mathcal{L} \) given by Eq. (13) has two misprints: the element (5,9) should be \( -\frac{1}{\rho} a \) rather than \( \frac{1}{\rho} a \) and the element (7,6) should be \( a \) rather than \( -a \). The results reported in the paper have been obtained from the correct matrix \( \mathcal{L} \).

The numerical value given in the paper for the diagonal element \( c_3(a) \) is based on numerical calculations done by Ikenberry and Truesdell [J. Rat. Mech. Anal. 5, 1 (1956)]. A more accurate evaluation [Z. Alterman, K. Frankowski, and C. L. Pekeris, Astrophys. J. Suppl. Ser. 7, 291 (1962/3)] yields \( c_3(a) = 4\alpha(a) + 1.873\nu \), which leads to a modified value for the critical shear rate: \( \alpha_c \approx 6.845\nu \).

Surface-Tension-Gradient-Induced Pattern Formation in Monolayers

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We regret that there was a misspelling on the name of the last author. It should be H. Ringsdorf. The correct names of the authors should read as follows: Mu Wang, G. Wildburg, J. H. van Esch, P. Bennema, R. J. M. Nolte, and H. Ringsdorf.